VS-25TTS08S-M3, VS-25TTS12S-M3 Series

Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A



Anode 2, 4	Э
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	J
1 Cathode	3 Gate

PRODUCT SUMMARY				
Package	TO-263AB (D ² PAK)			
Diode variation	Single SCR			
I _{T(AV)}	16 A			
V _{DRM} /V _{RRM}	800 V, 1200 V			
V _{TM}	1.25 V			
I _{GT}	45 mA			
TJ	-40 to +125 °C			

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912







APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5				
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A			
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0				

Note

T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	16	۸		
I _{RMS}		25	Α		
V _{RRM} /V _{DRM}		800 to 1200	V		
I _{TSM}		350	А		
V _T	16 A, T _J = 25 °C	1.25	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA		
VS-25TTS08S-M3	800	800	10		
VS-25TTS12S-M3	1200	1200	- 10		



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VAL	UES	UNITS
PANAMETEN	STIMBUL	123	T CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6	
Maximum RMS on-state current	I _{RMS}			2	:5	Α
Maximum peak, one-cycle,		10 ms sine pulse,	rated V _{RRM} applied	3	00	
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50	
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4:	450 A ² s	
Maximum 1-t for fusing	1-1	10 ms sine pulse,	no voltage reapplied	630		A-S
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 m	s, no voltage reapplied	63	00	A²√s
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.	25	V
On-state slope resistance	r _t	T 105 90		12	2.0	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1	.0	V
Maximum various and divest leakage arrest	1 /1	T _J = 25 °C	V Dated V A	0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	V _R = Rated V _{RRM} /V _{DRM}	1	0	
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	-	150	mA
Maximum latching current	IL	Anode supply = 6 V, resistive load, T _J = 25 °C		20	00	
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max., linear to 80 %, V _{DRM} = R _g - k = Open		50	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1:	50	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	VV
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 10 °C	60	mA
		Anode supply = 6 V, resistive load, T _J = 25 °C	45	
		Anode supply = 6 V, resistive load, T _J = 125 °C	20	
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}			
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value		mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9		
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs	
Typical turn-off time	t _q	1J = 125	110		



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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/VV
Approximate weight			2	g
Approximate weight			0.07	OZ.
Marking daying		Case style D ² PAK (SMD-220)	25TT	S08S
Marking device			25TT	S12S

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

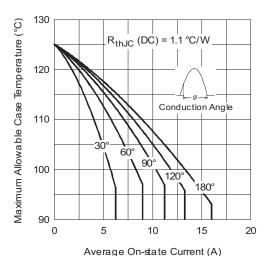


Fig. 1 - Current Rating Characteristics

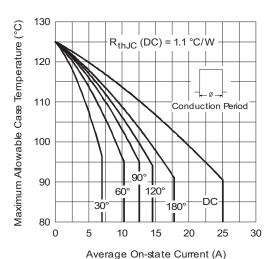


Fig. 2 - Current Rating Characteristics

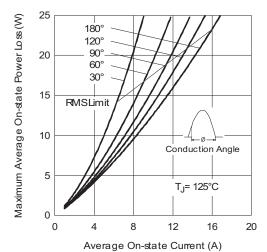
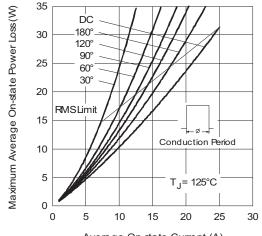


Fig. 3 - On-State Power Loss Characteristics



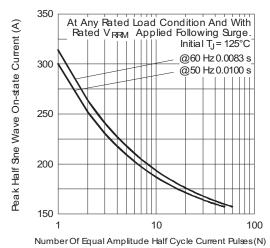
Average On-state Current (A)
Fig. 4 - On-State Power Loss Characteristics





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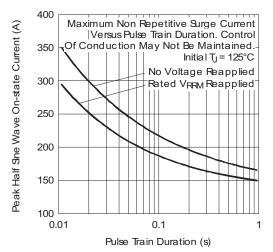


Fig. 6 - Maximum Non-Repetitive Surge Current



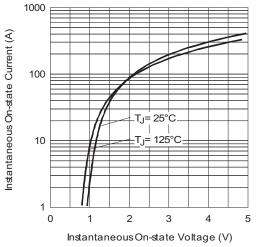
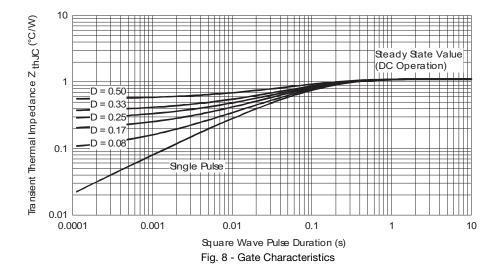


Fig. 7 - On-State Voltage Drop Characteristics



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08 = 800 V

12 = 1200 V

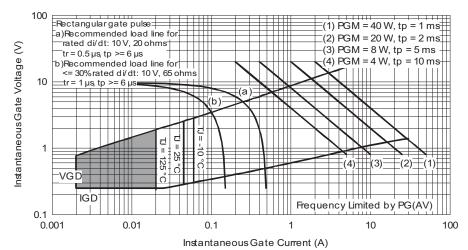
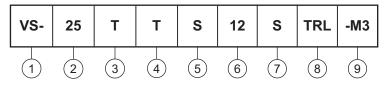


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

D٤	evi	ice	CO	de



- Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- **3** Circuit configuration:
 - T = single thyristor
- 4 Package:
 - $T = D^2PAK$
- 5 Type of silicon:
 - S = standard recovery rectifier
- 6 Voltage rating: voltage code x 100 = V_{RRM} -
- 7 S = surface mountable
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- g -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-25TTS08S-M3	50	1000	Antistatic plastic tubes			
VS-25TTS08STRR-M3	800	800	13" diameter reel			
VS-25TTS08STRL-M3	800	800	13" diameter reel			
VS-25TTS12S-M3	50	1000	Antistatic plastic tubes			
VS-25TTS12STRR-M3	800	800	13" diameter reel			
VS-25TTS12STRL-M3	800	800	13" diameter reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95046			
Part marking information	www.vishay.com/doc?95444			
Packaging information	www.vishay.com/doc?95032			



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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